

## AMENDMENTS TO THE SPECIFICATION

- Please amend the Title which begins on page 1, line 1, as follows:

~~CMP-PROCESSED INTERCONNECT~~  
~~CAP IN INTEGRATED~~  
~~CIRCUITS~~METHOD OF  
MANUFACTURING AN INTEGRATED  
CIRCUIT WITH LOW SOLIBILITY  
METAL-CONDUCTOR  
INTERCONNECT CAP

- Please amend the Cross-Reference to Related Application(s) section, which begins on page 1, line 3, as follows:

### CROSS-REFERENCE TO RELATED APPLICATION(S)

This is a divisional application of co-pending application serial number: 10/016,024,  
<sup>1</sup> Now U.S. Pat. 6,657,303  
filed December 12, 2002, which This application claims the benefit of U.S. Provisional patent  
application serial number 60/256,419 filed December 18, 2000.

- Please amend the Disclosure of the Invention section, which begins on page 4, line 21, as follows:

### DISCLOSURE OF THE INVENTION

~~The present invention provides an integrated circuit having a silicon substrate with a semiconductor device. A device oxide layer is on the silicon substrate and has an opening provided therein. A barrier layer lines the opening, with a seed layer lining the barrier layer, and a conductor core fills the opening over the seed layer. A low solubility metal conductor interconnect cap is disposed over the conductor core and seed layer and is capped with a~~